

Freescale Semiconductor
Technical Data

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RF Power Field Effect Transistors

N-Channel Enhancement-Mode Lateral MOSFETs

Designed for broadband commercial and industrial applications with frequencies from 400 to 500 MHz. The high gain and broadband performance of these devices make them ideal for large-signal, common-source amplifier applications in 28-volt base station equipment.

- Typical Single-Carrier N-CDMA Performance @ 465 MHz: $V_{DD} = 28$ Volts, $I_{DQ} = 1250$ mA, $P_{out} = 28$ Watts Avg., IS-95 CDMA (Pilot, Sync, Paging, Traffic Codes 8 Through 13). Channel Bandwidth = 1.2288 MHz. PAR = 9.8 dB @ 0.01% Probability on CCDF.
Power Gain — 21 dB
Drain Efficiency — 30%
ACPR @ 750 kHz Offset — -47.6 dBc in 30 kHz Bandwidth
- Capable of Handling 10:1 VSWR, @ 28 Vdc, 465 MHz, 140 Watts CW Output Power
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Internally Matched for Ease of Use
- Qualified Up to a Maximum of 32 V_{DD} Operation
- Integrated ESD Protection
- Lower Thermal Resistance Package
- Low Gold Plating Thickness on Leads, 40 μ " Nominal.
- Pb-Free and RoHS Compliant
- In Tape and Reel. R3 Suffix = 250 Units per 56 mm, 13 inch Reel.

MRF5S4140HR3
MRF5S4140HSR3

465 MHz, 28 W AVG., 28 V
SINGLE N-CDMA
LATERAL N-CHANNEL
RF POWER MOSFETs

CASE 465-06, STYLE 1
NI-780
MRF5S4140HR3

CASE 465A-06, STYLE 1
NI-780S
MRF5S4140HSR3

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +65	Vdc
Gate-Source Voltage	V_{GS}	-0.5, +15	Vdc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25 $^\circ\text{C}$	P_D	427 2.4	W W/ $^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to +150	$^\circ\text{C}$
Operating Junction Temperature	T_J	200	$^\circ\text{C}$

Table 2. Thermal Characteristics

Characteristic	Symbol	Value (1,2)	Unit
Thermal Resistance, Junction to Case Case Temperature 73 $^\circ\text{C}$, 140 W CW Case Temperature 74 $^\circ\text{C}$, 28 W CW	$R_{\theta JC}$	0.41 0.47	$^\circ\text{C}/\text{W}$

1. MTTF calculator available at <http://www.freescale.com/rf>. Select Tools/Software/Application Software/Calculators to access the MTTF calculators by product.
2. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

NOTE - CAUTION - MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.



Table 3. ESD Protection Characteristics

Test Conditions	Class
Human Body Model (per JESD22-A114)	1C (Minimum)
Machine Model (per EIA/JESD22-A115)	A (Minimum)
Charge Device Model (per JESD22-C101)	IV (Minimum)

Table 4. Moisture Sensitivity Level

Test Methodology	Rating	Package Peak Temperature	Unit
Per JESD 22-A113, IPC/JEDEC J-STD-020	3	260	°C

Table 5. Electrical Characteristics($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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Off Characteristics

Zero Gate Voltage Drain Leakage Current ($V_{DS} = 68\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}			10	μAdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 26\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}			1	μAdc
Gate-Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}			1	μAdc

On Characteristics

Gate Threshold Voltage ($V_{DS} = 10\text{ Vdc}$, $I_D = 40\text{ }\mu\text{A}$)	$V_{GS(th)}$	2	2.8	3.5	Vdc
Gate Quiescent Voltage ($V_{DS} = 26\text{ Vdc}$, $I_D = 950\text{ mA}$)	$V_{GS(Q)}$		3.7		Vdc
Drain-Source On-Voltage ($V_{GS} = 10\text{ Vdc}$, $I_D = 2.0\text{ Adc}$)	$V_{DS(on)}$		0.21	0.3	Vdc
Forward Transconductance ($V_{DS} = 10\text{ Vdc}$, $I_D = 6\text{ Adc}$)	g_{fs}		7		S

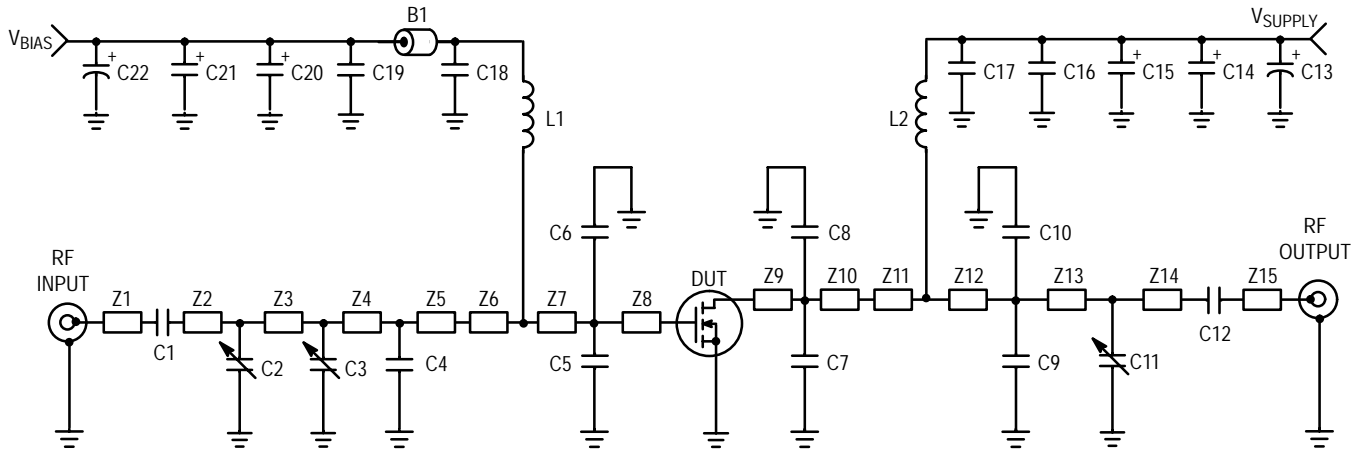
Dynamic Characteristics ⁽¹⁾

Output Capacitance ($V_{DS} = 26\text{ Vdc}$, 30 mV(rms)ac @ 1 MHz , $V_{GS} = 0\text{ Vdc}$)	C_{OSS}		70		pF
Reverse Transfer Capacitance ($V_{DS} = 26\text{ Vdc}$, 30 mV(rms)ac @ 1 MHz , $V_{GS} = 0\text{ Vdc}$)	C_{RSS}		2.2		pF

Functional Tests (In Freescale Test Fixture, 50 ohm system) $V_{DS} = 26\text{ Vdc}$, $I_{DQ} = 950\text{ mA}$, $P_{out} = 20\text{ W Avg.}$ N-CDMA, $f = 880\text{ MHz}$, Single-Carrier N-CDMA, 1.2288 MHz Channel Bandwidth Carrier. ACPR measured in 30 kHz Bandwidth 150 kHz Offset. PAR = 9.8 dB @ 0.01% Probability on CCDF

Power Gain	G_{ps}	18	19.5		dB
Drain Efficiency	η	26	28		%
Adjacent Channel Power Ratio	ACPR		-46.8	-45	dBc
Input Return Loss	IRL		-19	-9	dB

1. Part is internally input matched.

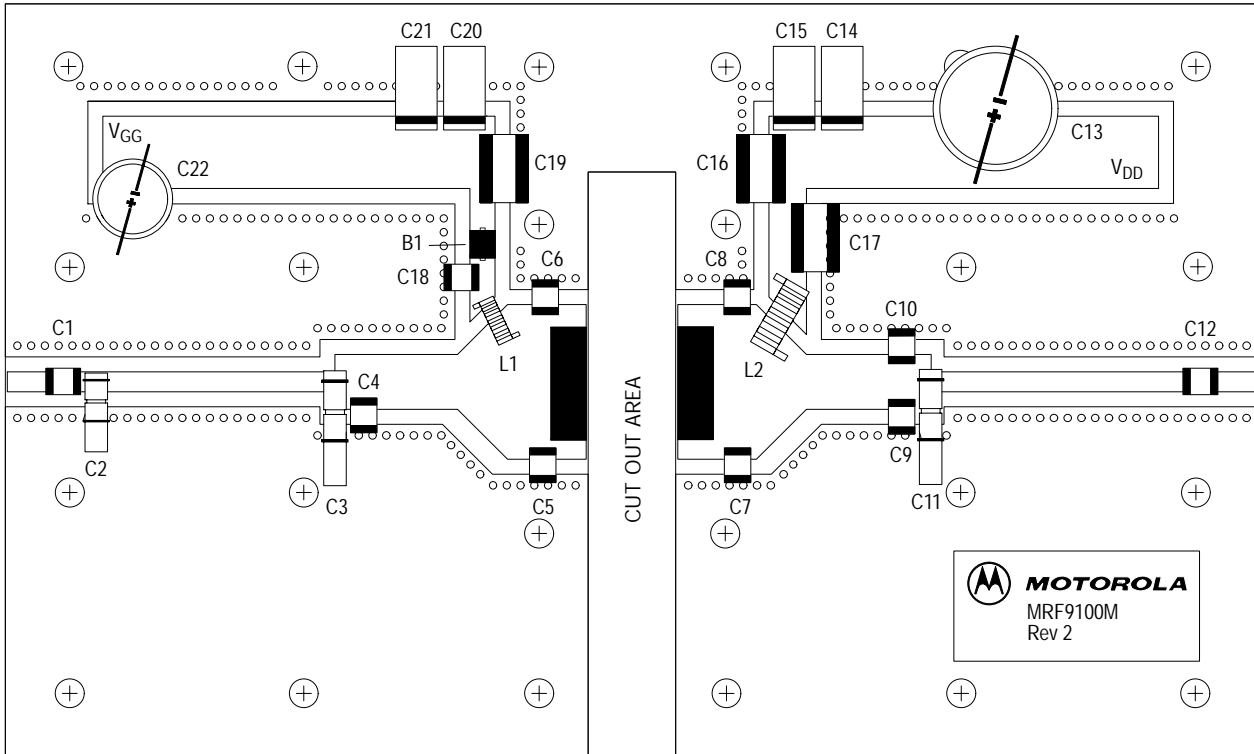


Z1, Z15	0.200 x 0.080 Microstrip	Z8	0.163 x 0.620 Microstrip
Z2	0.105 x 0.080 Microstrip	Z9	0.238 x 0.620 Microstrip
Z3	0.954 x 0.080 Microstrip	Z10	0.077 x 0.620 Microstrip
Z4	0.115 x 0.220 Microstrip	Z12	0.381 x 0.220 Microstrip
Z5	0.375 x 0.220 Microstrip	Z13	0.114 x 0.220 Microstrip
Z6, Z11	0.200 x 0.220 x 0.620 Taper	Z14	1.052 x 0.080 Microstrip
Z7	0.152 x 0.620 Microstrip	PCB	Arlon GX0300, 0.030 $r = 2.55$

Figure 1. MRF5S9100NR1(NBR1)/MR1(MBR1) Test Circuit Schematic

Table 6. MRF5S9100NR1(NBR1)/MR1(MBR1) Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
B1	Ferrite Bead, Surface Mount	2743019447	Fair-Rite
C1, C12, C18	18 pF Chip Capacitors	100B180JP 500X	ATC
C2	0.6-4.5 pF Variable Capacitor, Gigatrim	27271SL	Johanson Dielectrics
C3, C11	0.8-8.0 pF Variable Capacitors, Gigatrim	27291SL	Johanson Dielectrics
C4	6.2 pF Chip Capacitor	100B6R2JP 500X	ATC
C5, C6	12 pF Chip Capacitors	100B120JP 500X	ATC
C7, C8	11 pF Chip Capacitors	100B110JP 500X	ATC
C9, C10	5.1 pF Chip Capacitors	100B5R1JP 500X	ATC
C13	470 μ F, 63 V Electrolytic Capacitor	NACZF471M63V	Nippon
C14, C15	22 μ F, 50 V Tantalum Capacitors	T491X226K035AS	Kemet
C16, C17, C19	0.56 μ F, 50 V Chip Capacitors	C1825C564J5GAC	Kemet
C20, C21	47 μ F, 16 V Tantalum Capacitors	T491D4T6K016AS	Kemet
C22	100 μ F, 50 V Electrolytic Capacitor	515D107M050BB6A	Multicomp
L1	7.15 nH Inductor	1606-7	CoilCraft
L2	22 nH Inductor	B07T-5	CoilCraft



Freescale has begun the transition of marking Printed Circuit Boards (PCBs) with the Freescale Semiconductor signature/logo. PCBs may have either Motorola or Freescale markings during the transition period. These changes will have no impact on form, fit or function of the current product.

Figure 2. MRF5S9100NR1(NBR1)/MR1(MBR1) Test Circuit Component Layout

TYPICAL CHARACTERISTICS

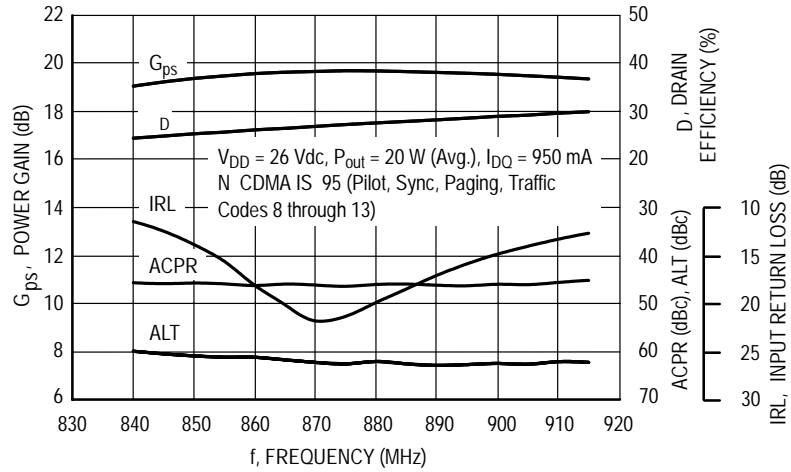


Figure 3. IS-95 Broadband Performance @ $P_{out} = 20$ Watts Avg.

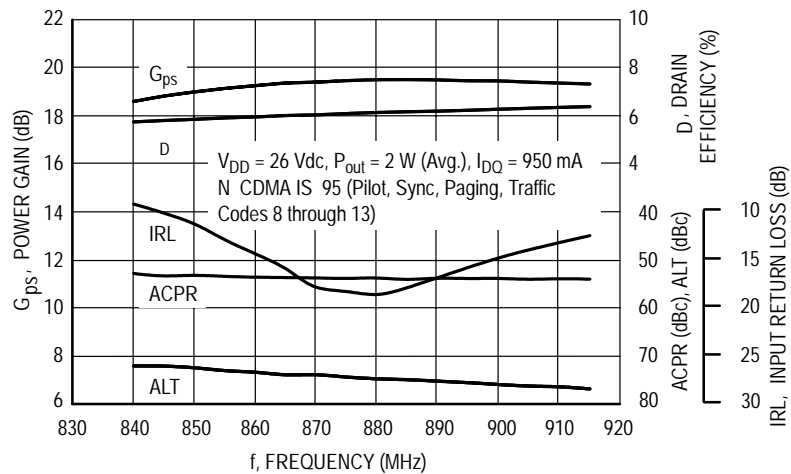


Figure 4. IS-95 Broadband Performance @ $P_{out} = 2$ Watts Avg.

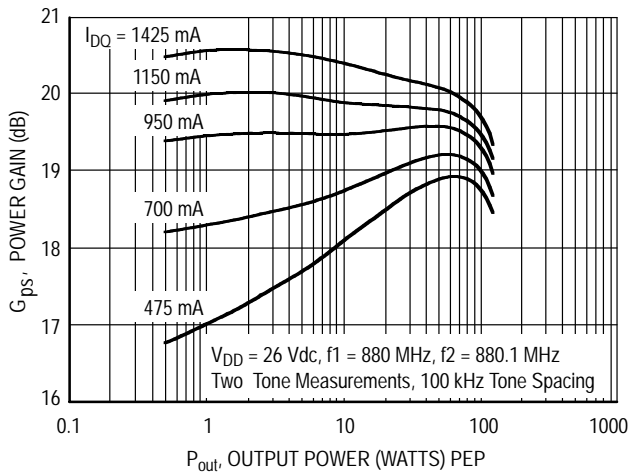


Figure 5. Two-Tone Power Gain versus Output Power

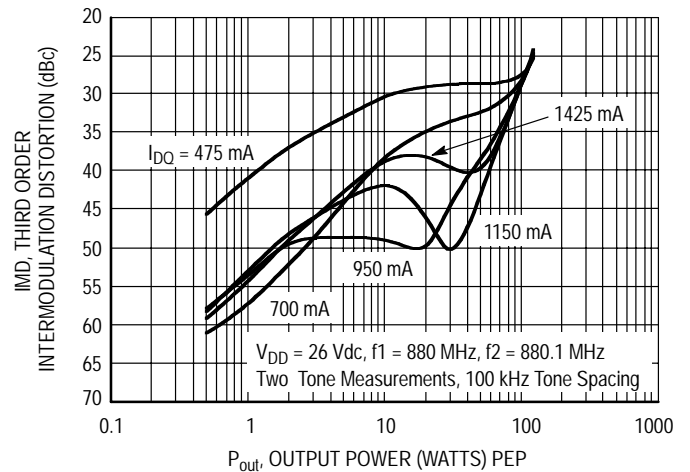


Figure 6. Third Order Intermodulation Distortion versus Output Power

TYPICAL CHARACTERISTICS

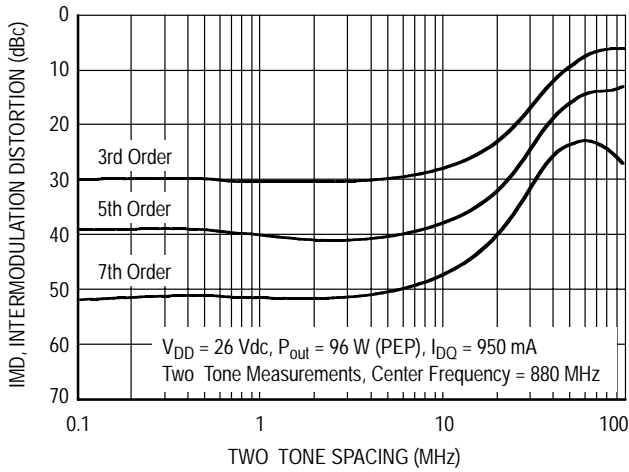


Figure 7. Intermodulation Distortion Products versus Tone Spacing

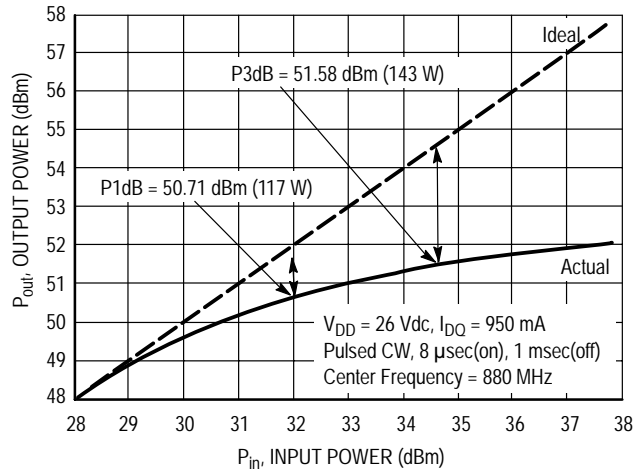


Figure 8. Pulse CW Output Power versus Input Power

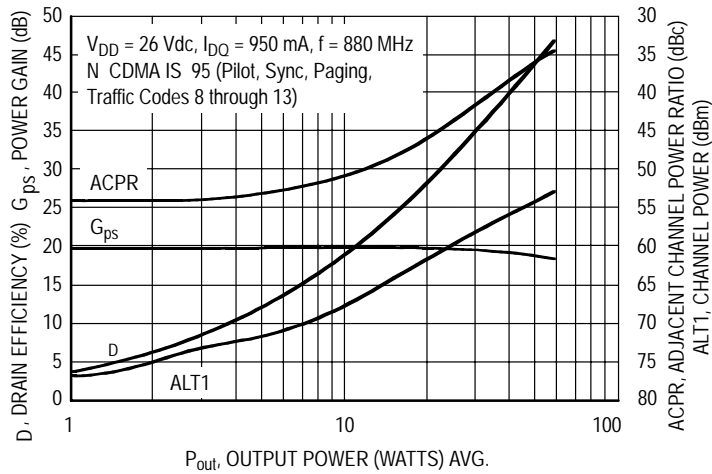


Figure 9. Single-Carrier N-CDMA ACPR, Power Gain, Efficiency and ALT1 versus Output Power

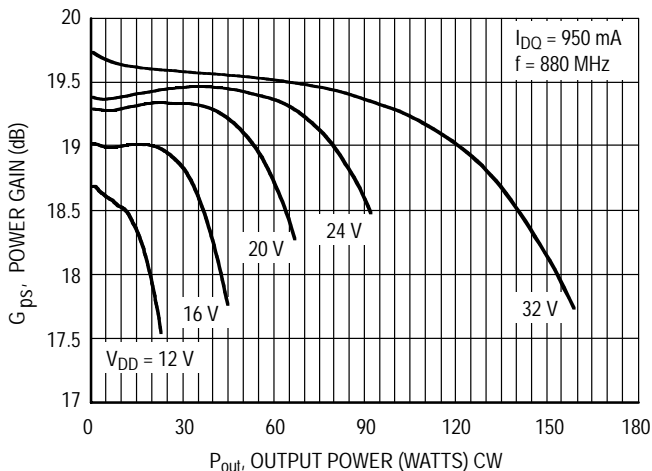
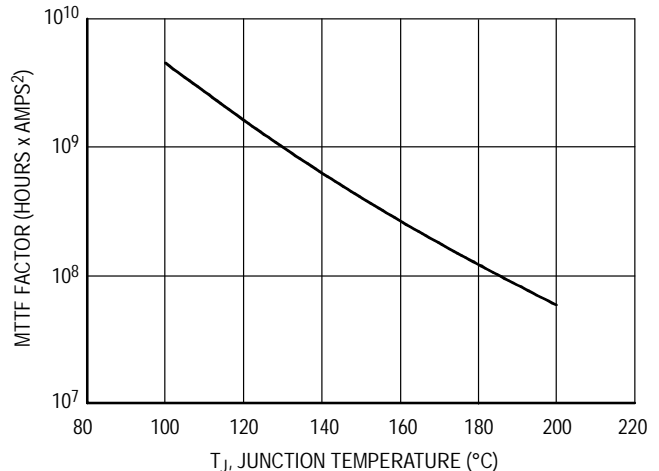
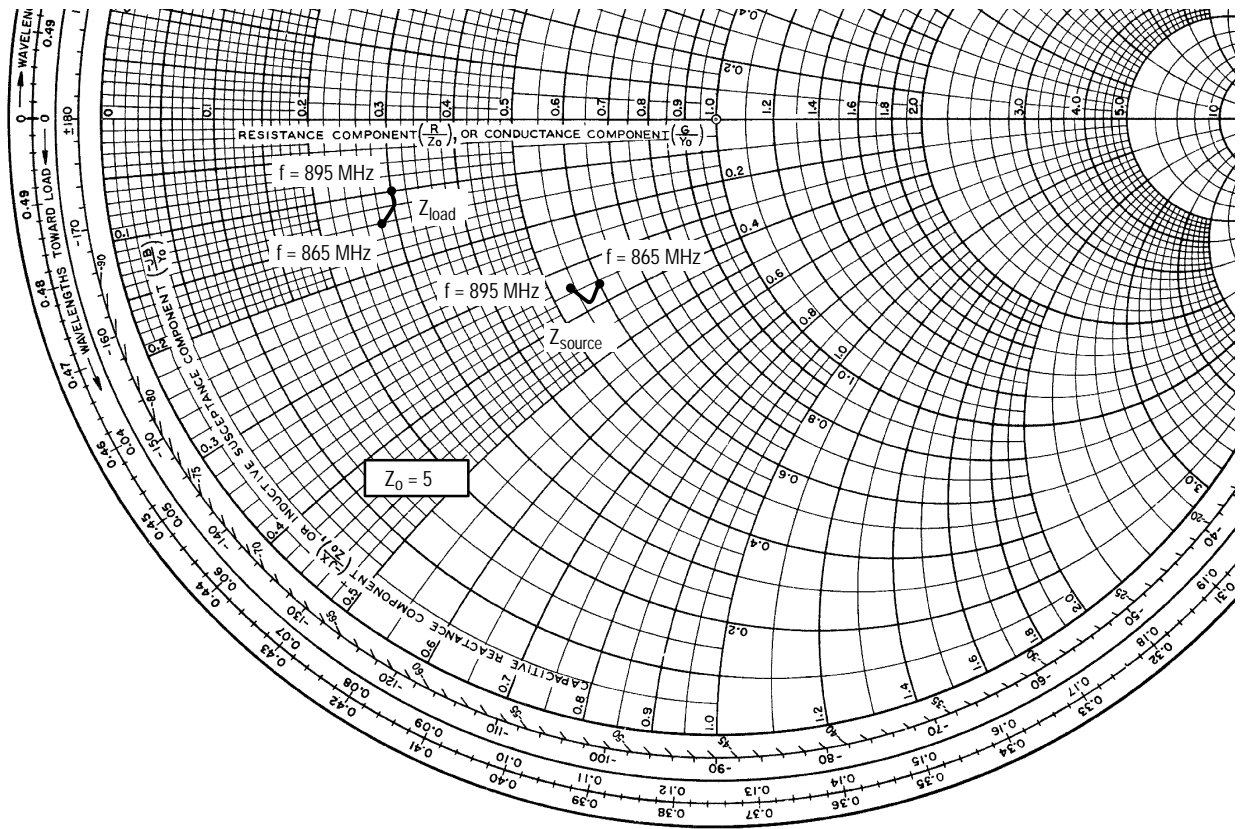


Figure 10. Power Gain versus Output Power



This above graph displays calculated MTTF in hours x ampere² drain current. Life tests at elevated temperatures have correlated to better than -10% of the theoretical prediction for metal failure. Divide MTTF factor by I_D^2 for MTTF in a particular application.

Figure 11. MTTF Factor versus Junction Temperature



$V_{DD} = 26$ Vdc, $I_{DQ} = 950$ mA, $P_{out} = 20$ W Avg.

f MHz	Z_{source}	Z_{load}
865	$3.0 - j1.8$	$1.4 - j0.7$
880	$2.8 - j1.9$	$1.5 - j0.6$
895	$2.7 - j1.7$	$1.5 - j0.5$

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

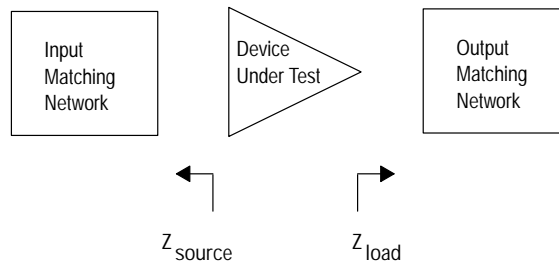
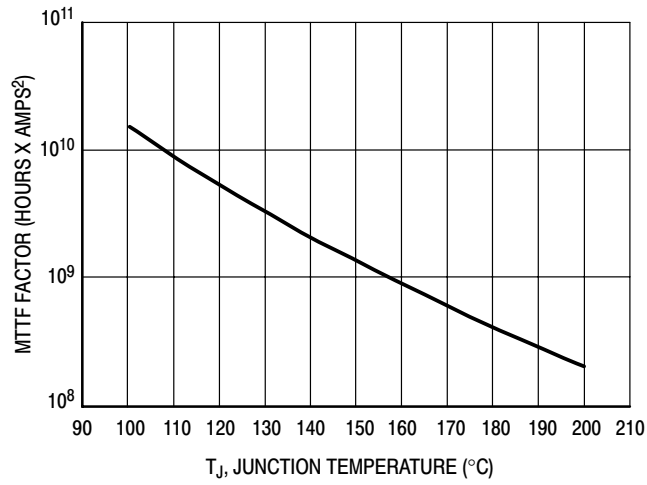


Figure 12. Series Equivalent Source and Load Impedance

TYPICAL CHARACTERISTICS



This above graph displays calculated MTTF in hours x ampere² drain current. Life tests at elevated temperatures have correlated to better than $\pm 10\%$ of the theoretical prediction for metal failure. Divide MTTF factor by I_D^2 for MTTF in a particular application.

Figure 24. MTTF Factor versus Junction Temperature

N-CDMA TEST SIGNAL

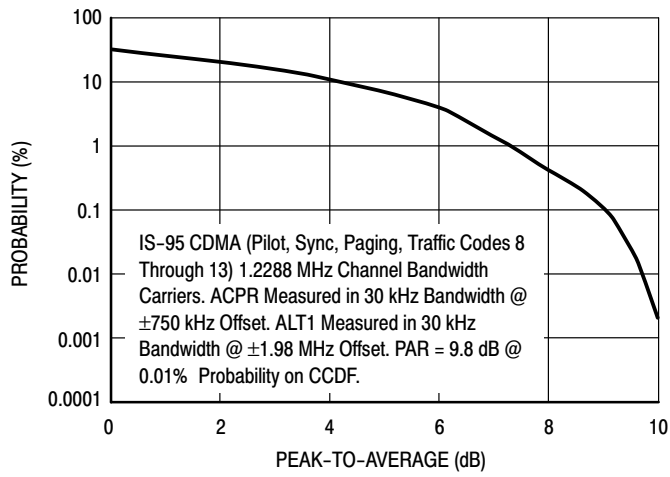


Figure 25. Single-Carrier CCDF N-CDMA

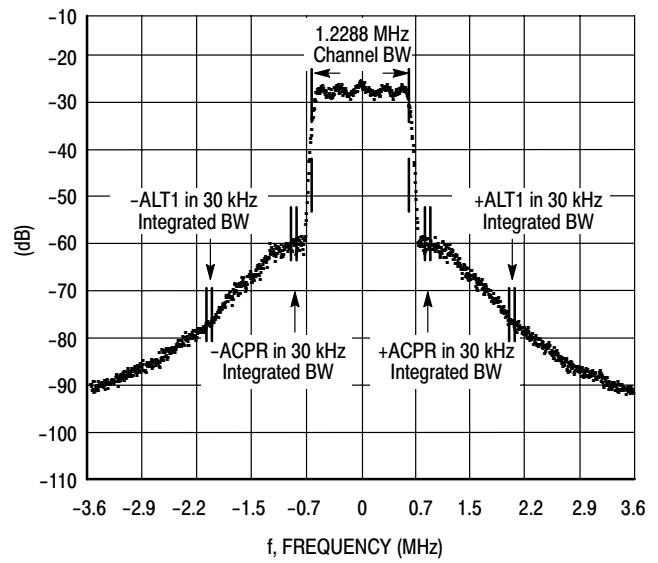
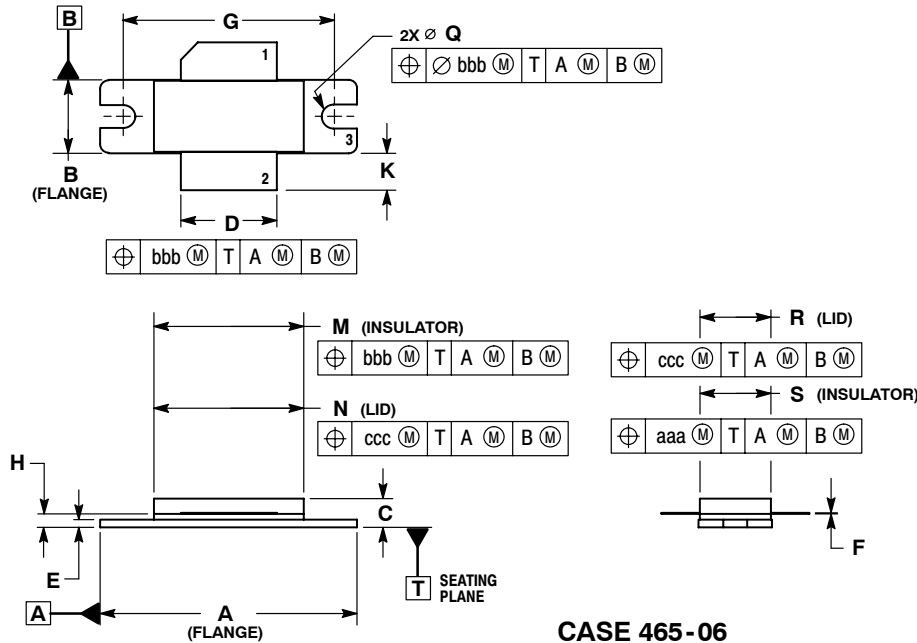


Figure 26. Single-Carrier N-CDMA Spectrum

PACKAGE DIMENSIONS

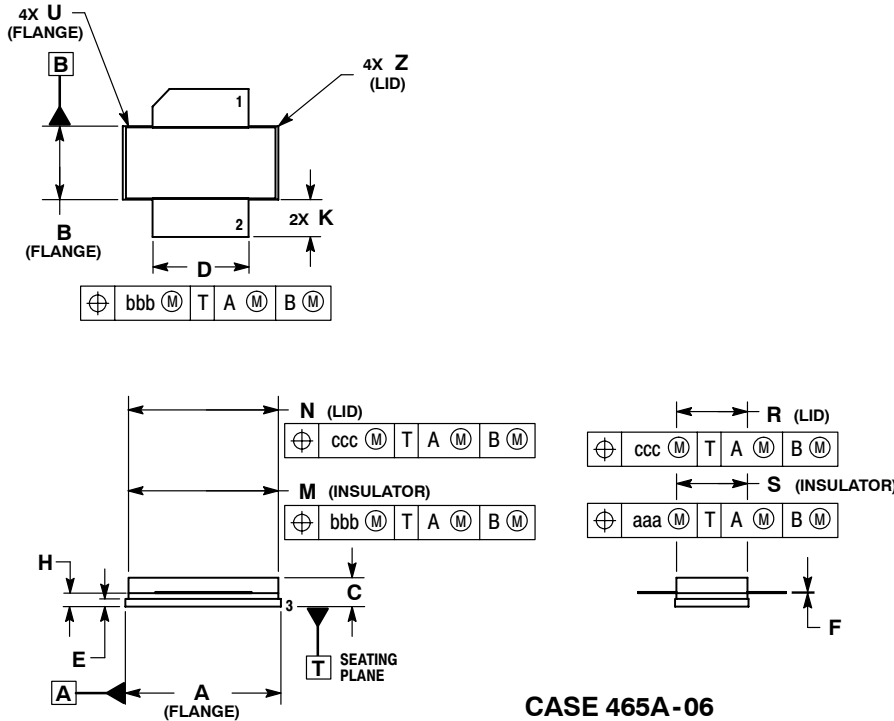


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
 2. CONTROLLING DIMENSION: INCH.
 3. DELETED
 4. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.335	1.345	33.91	34.16
B	0.380	0.390	9.65	9.91
C	0.125	0.170	3.18	4.32
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
G	1.100 BSC		27.94 BSC	
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.774	0.786	19.66	19.96
N	0.772	0.788	19.60	20.00
Q	∅ 0.118	∅ 0.138	∅ 3.00	∅ 3.51
R	0.365	0.375	9.27	9.53
S	0.365	0.375	9.27	9.52
aaa	0.005 REF		0.127 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

- STYLE 1:
1. DRAIN
 2. GATE
 3. SOURCE

**CASE 465-06
ISSUE G
NI-780
MRF5S4140HR3**



- NOTES:
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 2. CONTROLLING DIMENSION: INCH.
 3. DELETED
 4. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.805	0.815	20.45	20.70
B	0.380	0.390	9.65	9.91
C	0.125	0.170	3.18	4.32
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.774	0.786	19.61	20.02
N	0.772	0.788	19.61	20.02
R	0.365	0.375	9.27	9.53
S	0.365	0.375	9.27	9.52
U	---	0.040	---	1.02
Z	---	0.030	---	0.76
aaa	0.005 REF		0.127 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

- STYLE 1:
1. DRAIN
 2. GATE
 5. SOURCE

**CASE 465A-06
ISSUE H
NI-780S
MRF5S4140HSR3**

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